

## ABSTRACT OF THE DISCLOSURE

A light emitting diode (LED) of a double hetero-junction type has a light-emitting layer of a GaAlInP material, a p-type cladding layer and an n-type cladding layer sandwiching the light-emitting layer therebetween, a p-side electrode formed on the p-type cladding layer side, and an n-side electrode formed on the n-type cladding layer side. The p-type cladding layer consists of a first p-type cladding layer positioned closer to the light-emitting layer and having a lower aluminum content and a lower impurity concentration, and a second p-type cladding layer positioned less closer to the light-emitting layer and having a higher aluminum content and a higher impurity concentration. The LED also has a current blocking layer below the p-side electrode for locally blocking electric current flowing from the p-side electrode to the n-side electrode.